



ICMOVPE XXII

July 12 (Sun.) – 17 (Fri.), 2026

ICC JEJU, Jeju Island, Korea

Name of Company	L&D Inc.	Company Logo
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Exhibitor Introduction	L&D Inc. specializes in AlN-based epitaxial wafer solutions for next-generation RF, power, and UV device applications. Our core technology is the growth of thick, high-quality AlN layers with excellent crystalline quality, smooth surface morphology, and stable material uniformity. Based on our in-house MOCVD growth technology, L&D Inc. develops AlN templates and AlN buffer-based GaN HEMT epiwafers on SiC substrates. These epiwafer platforms are designed to support high-frequency and high-power semiconductor devices, including RF power devices, 5G/6G communications, satellite communication, radar systems, power electronics, and UV devices. L&D Inc. is committed to providing reliable AlN-based epiwafer products by continuously improving AlN growth quality, thickness control, surface uniformity, and device-oriented epitaxial structures.	
Exhibit Product	4-inch Customized AlN Buffer-based Epitaxial Wafers AlN on SiC Template GaN & AlGaN Channel HEMT Epiwafers Doped GaN & AlN Structures 6-inch AlN Template	